

Ching-Hwa Ho

List of Publications by Year in descending order

Source: <https://exaly.com/author-pdf/5839074/publications.pdf>

Version: 2024-02-01

191
papers

6,406
citations

66343

42
h-index

79698

73
g-index

191
all docs

191
docs citations

191
times ranked

6810
citing authors

| # | ARTICLE | IF | CITATIONS |
|----|---|------|-----------|
| 1 | An all two-dimensional vertical heterostructure graphene/CuInP ₂ S ₆ /MoS ₂ for negative capacitance field effect transistor. Nanotechnology, 2022, 33, 125703. | 2.6 | 11 |
| 2 | Internal Built-In Electric Fields at Organic-Inorganic Interfaces of Two-Dimensional Ruddlesden-Popper Perovskite Single Crystals. ACS Applied Materials & Interfaces, 2022, 14, 19818-19825. | 8.0 | 3 |
| 3 | Formation of van der Waals Stacked n Homojunction Optoelectronic Device of Multilayered ReSe ₂ by Cr Doping. Advanced Optical Materials, 2022, 10, . | 7.3 | 8 |
| 4 | Molybdenum disulfide homogeneous junction diode fabrication and rectification characteristics. Japanese Journal of Applied Physics, 2022, 61, 086504. | 1.5 | 1 |
| 5 | Van der Waals Heterostructure Photodetectors with Bias-Selectable Infrared Photoresponses. ACS Applied Materials & Interfaces, 2022, 14, 32665-32674. | 8.0 | 18 |
| 6 | Dual phase two-color emission observed in van der Waals GaTe planes. Applied Surface Science, 2021, 542, 148593. | 6.1 | 14 |
| 7 | The Study of Optical Properties of III-VI Defect Semiconductor Group Compounds Ga ₂ S ₃ , Ga ₂ Se ₃ , In ₂ S ₃ , and In ₂ Se ₃ . Advanced Photonics Research, 2021, 2, 2000110. | 3.6 | 8 |
| 8 | Investigations of Electron-Electron and Interlayer Electron-Phonon Coupling in van der Waals hBN/WSe ₂ /hBN Heterostructures by Photoluminescence Excitation Experiments. Materials, 2021, 14, 399. | 2.9 | 8 |
| 9 | The band-edge excitons observed in few-layer NiPS ₃ . Npj 2D Materials and Applications, 2021, 5, . | 7.9 | 21 |
| 10 | Carrier-capture-assisted optoelectronics based on van der Waals materials to imitate medicine-acting metaplasticity. Npj 2D Materials and Applications, 2021, 5, . | 7.9 | 7 |
| 11 | Photoactive Electro-Controlled Visual Perception Memory for Emulating Synaptic Metaplasticity and Hebbian Learning. Advanced Functional Materials, 2021, 31, 2105345. | 14.9 | 18 |
| 12 | Thermoreflectance characterization of the band-edge excitons observed in multilayered CuInP ₂ S ₆ . FlatChem, 2021, 29, 100290. | 5.6 | 8 |
| 13 | Probing negatively charged and neutral excitons in MoS ₂ /hBN and hBN/MoS ₂ /hBN van der Waals heterostructures. Nanotechnology, 2021, 32, 145717. | 2.6 | 17 |
| 14 | Upconversion of Light into Bright Intravalley Excitons via Dark Intervalley Excitons in hBN-Encapsulated WSe ₂ Monolayers. ACS Nano, 2021, 15, 19165-19174. | 14.6 | 18 |
| 15 | Nanowire Grid Polarization and Polarized Excitonic Emission Observed in Multilayer GaTe. Journal of Physical Chemistry Letters, 2020, 11, 608-617. | 4.6 | 20 |
| 16 | Multilayer GaSe/InSe Heterointerface-Based Devices for Charge Transport and Optoelectronics. ACS Applied Nano Materials, 2020, 3, 11769-11776. | 5.0 | 18 |
| 17 | Ga ₂ Se ₃ Defect Semiconductors: The Study of Direct Band Edge and Optical Properties. ACS Omega, 2020, 5, 18527-18534. | 3.5 | 14 |
| 18 | Inverse paired-pulse facilitation in neuroplasticity based on interface-boosted charge trapping layered electronics. Nano Energy, 2020, 77, 105258. | 16.0 | 22 |

| # | ARTICLE | IF | CITATIONS |
|----|---|------|-----------|
| 19 | Tuning Interface Barrier in 2D BP/ReSe ₂ Heterojunctions in Control of Optoelectronic Performances and Energy Conversion Efficiencies. ACS Photonics, 2020, 7, 2886-2895. | 6.6 | 20 |
| 20 | Oxidation-boosted charge trapping in ultra-sensitive van der Waals materials for artificial synaptic features. Nature Communications, 2020, 11, 2972. | 12.8 | 83 |
| 21 | Optical and Thermoelectric Properties of Surface-Oxidation Sensitive Layered Zirconium Dichalcogenides ZrS ₂ xSex (x = 0, 1, 2) Crystals Grown by Chemical Vapor Transport. Crystals, 2020, 10, 327. | 2.2 | 18 |
| 22 | Study of Structural, Thermoelectric, and Photoelectric Properties of Layered Tin Monochalcogenides SnX (X = S, Se) for Energy Application. ACS Applied Energy Materials, 2020, 3, 4896-4905. | 5.1 | 22 |
| 23 | High-responsivity broad-band sensing and photoconduction mechanism in direct-Gap In ₂ Se ₃ nanosheet photodetectors. Nanotechnology, 2020, 31, 465201. | 2.6 | 23 |
| 24 | Photoluminescence and time-resolved photoluminescence study of GaSe _{1-x} S _x mixed crystal. , 2020, , . | | 0 |
| 25 | Temperature-dependent ultraviolet photoluminescence in hierarchical Zn, ZnO and ZnO/Zn nanostructures. Nanoscale, 2019, 11, 13385-13396. | 5.6 | 32 |
| 26 | Mode-locked Tm-doped fiber laser with large modulation depth ReS _{1.02} Se _{0.98} nanosheet saturable absorber. Japanese Journal of Applied Physics, 2019, 58, 100907. | 1.5 | 5 |
| 27 | High-Mobility InSe Transistors: The Nature of Charge Transport. ACS Applied Materials & Interfaces, 2019, 11, 35969-35976. | 8.0 | 23 |
| 28 | Multifunctional full-visible-spectrum optoelectronics based on a van der Waals heterostructure. Nano Energy, 2019, 66, 104107. | 16.0 | 28 |
| 29 | InSe Tribotronic Transistors: Low Voltage Operational, Low Power Consuming, and High Sensitive Tactile Switch Based on 2D Layered InSe Tribotronics (Adv. Funct. Mater. 19/2019). Advanced Functional Materials, 2019, 29, 1970125. | 14.9 | 0 |
| 30 | Few-layer ReS ₂ (1-x)Se _{2x} nanoflakes for noise-like pulse generation in a mode-locked ytterbium-doped fiber laser. Journal of Materials Chemistry C, 2019, 7, 6900-6904. | 5.5 | 19 |
| 31 | Analog Circuit Applications Based on All 2D Ambipolar ReSe ₂ Field Effect Transistors. Advanced Functional Materials, 2019, 29, 1809011. | 14.9 | 36 |
| 32 | Low Voltage Operational, Low Power Consuming, and High Sensitive Tactile Switch Based on 2D Layered InSe Tribotronics. Advanced Functional Materials, 2019, 29, 1809119. | 14.9 | 28 |
| 33 | Effect of Cr on the Structure and Property of Mo _{1-x} Cr _x Se ₂ (0 ≤ x ≤ 0.2) and Cr ₂ Se ₃ . ACS Applied Electronic Materials, 2019, 1, 370-378. | 4.3 | 12 |
| 34 | Complete-series excitonic dipole emissions in few layer ReS ₂ and ReSe ₂ observed by polarized photoluminescence spectroscopy. Nano Energy, 2019, 56, 641-650. | 16.0 | 49 |
| 35 | Synthesis, optical characterization, and environmental applications of In ²⁺ -Ga ₂ O ₃ nanowires. , 2019, , 67-90. | | 8 |
| 36 | Ternary ReS ₂ (1-x)Se _{2x} alloy saturable absorber for passively Q-switched and mode-locked erbium-doped all-fiber lasers. Photonics Research, 2019, 7, 283. | 7.0 | 26 |

| # | ARTICLE | IF | CITATIONS |
|----|--|------|-----------|
| 37 | Ultraefficient Ultraviolet and Visible Light Sensing and Ohmic Contacts in High-Mobility InSe Nanoflake Photodetectors Fabricated by the Focused Ion Beam Technique. ACS Applied Materials & Interfaces, 2018, 10, 5740-5749. | 8.0 | 45 |
| 38 | Curvature-dependent flexible light emission from layered gallium selenide crystals. RSC Advances, 2018, 8, 2733-2739. | 3.6 | 21 |
| 39 | Temperature dependence of direct and indirect band gaps of Bi ₁₃ Te ₁₈ hexagonal rod crystals. Materials Chemistry and Physics, 2018, 206, 71-75. | 4.0 | 8 |
| 40 | Polarization Photoelectric Conversion in Layered GeS. Advanced Optical Materials, 2018, 6, 1701194. | 7.3 | 36 |
| 41 | High Mobilities in Layered InSe Transistors with Indium-Encapsulation-Induced Surface Charge Doping. Advanced Materials, 2018, 30, e1803690. | 21.0 | 101 |
| 42 | Dynamic tungsten diselenide nanomaterials: supramolecular assembly-induced structural transition over exfoliated two-dimensional nanosheets. Chemical Science, 2018, 9, 5452-5460. | 7.4 | 22 |
| 43 | In-Plane Axially Enhanced Photocatalysis by Re ₄ Diamond Chains in Layered ReS ₂ . Journal of Physical Chemistry C, 2018, 122, 18776-18784. | 3.1 | 14 |
| 44 | The Study of Near-Band-Edge Property in Oxygen-Incorporated ZnS for Acting as an Efficient Crystal Photocatalyst. ACS Omega, 2018, 3, 6351-6359. | 3.5 | 8 |
| 45 | Bending photoluminescence study of 2D layered GaSe. , 2018, , . | | 0 |
| 46 | Anisotropic Spectroscopy and Electrical Properties of 2D ReS ₂ (1- <i>x</i>)Se ₂ (<i>x</i>) Alloys with Distorted 1T Structure. Small, 2017, 13, 1603788. | 10.0 | 70 |
| 47 | The structure and opto-thermo electronic properties of a new (Bi(Bi ₂ S ₃) ₉) _{2/3} hexagonal nano-/micro-rod. Chemical Communications, 2017, 53, 3741-3744. | 4.1 | 14 |
| 48 | The study of flexible emission and photoconductivity in 2D layered InSe toward an applicable 1000-nm light emitter and absorber. Applied Physics A: Materials Science and Processing, 2017, 123, 1. | 2.3 | 9 |
| 49 | Direct and indirect light emissions from layered ReS ₂ Se(<i>x</i>)(<i>0</i>) Tj ETQq1 1.0,784314 rgBT / O _{2.6} 19 ⁵ | | |
| 50 | Direct identification of monolayer rhenium diselenide by an individual diffraction pattern. Nano Research, 2017, 10, 2535-2544. | 10.4 | 5 |
| 51 | Pressure-induced metallization and superconducting phase in ReS ₂ . Npj Quantum Materials, 2017, 2, . | 5.2 | 53 |
| 52 | Interplay Between Cr Dopants and Vacancy Clustering in the Structural and Optical Properties of WSe ₂ . ACS Nano, 2017, 11, 11162-11168. | 14.6 | 33 |
| 53 | Cleavage tendency of anisotropic two-dimensional materials: $\langle \text{mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML"} \rangle \langle \text{mml:mrow} \langle \text{mml:mi} \text{Re} \langle \text{mml:mi} \langle \text{mml:msub} \langle \text{mml:mi} \text{X} \langle \text{mml:mi} \langle \text{mml:mi} \text{and} \langle \text{mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML"} \rangle \langle \text{mml:mi} \text{Physical Review B, 2017, 96, .$ | 3.2 | 36 |
| 54 | Optical Study of High Quality <i>x</i> -ZnS Crystals for UV Photodiodes and Photoelectrochemical Applications. ChemistrySelect, 2017, 2, 9391-9395. | 1.5 | 2 |

| # | ARTICLE | IF | CITATIONS |
|----|--|------|-----------|
| 55 | Synthesis and Optical Characterization of Oxygen-Incorporated ZnS _{1-x} O _x for UV-Visible Color Palette Light-Emission Matter. ACS Omega, 2017, 2, 4514-4523. | 3.5 | 15 |
| 56 | High-Mobility InSe Transistors: The Role of Surface Oxides. ACS Nano, 2017, 11, 7362-7370. | 14.6 | 177 |
| 57 | Polarized Band-Edge Emission and Dichroic Optical Behavior in Thin Multilayer GeS. Advanced Optical Materials, 2017, 5, 1600814. | 7.3 | 45 |
| 58 | Optical and photodetector properties of stripe-like InS crystal. RSC Advances, 2016, 6, 97445-97448. | 3.6 | 8 |
| 59 | Synthesis of In ₂ S ₃ and Ga ₂ S ₃ crystals for oxygen sensing and UV photodetection. Sensors and Actuators A: Physical, 2016, 245, 119-126. | 4.1 | 49 |
| 60 | Synthesis and optical characterization of a high-quality ZnS substrate for optoelectronics and UV solar-energy conversion. RSC Advances, 2016, 6, 81053-81059. | 3.6 | 4 |
| 61 | Optical Characterization of Structural Quality in the Formation of In ₂ O ₃ Thin-Film Nanostructures. Journal of Physical Chemistry C, 2016, 120, 21983-21989. | 3.1 | 16 |
| 62 | Disorder engineering and conductivity dome in ReS ₂ with electrolyte gating. Nature Communications, 2016, 7, 12391. | 12.8 | 109 |
| 63 | Thickness-dependent carrier transport and optically enhanced transconductance gain in III-VI multilayer InSe. 2D Materials, 2016, 3, 025019. | 4.4 | 56 |
| 64 | Observation of near-band-edge photoluminescence and UV photoresponse in near-stoichiometric Zn ₂ SnO ₄ nanowires. Materials Research Express, 2016, 3, 066201. | 1.6 | 4 |
| 65 | 2D multilayer InSe – An applicable 1000 nm light emitter and absorber. , 2016, , . | | 2 |
| 66 | Optical Characterization of Strong UV Luminescence Emitted from the Excitonic Edge of Nickel Oxide Nanotowers. Scientific Reports, 2015, 5, 15856. | 3.3 | 20 |
| 67 | Bending Photoluminescence and Surface Photovoltaic Effect on Multilayer InSe 2D Microplate Crystals. Advanced Optical Materials, 2015, 3, 1750-1758. | 7.3 | 75 |
| 68 | Amorphous effect on the advancing of structural-phase transition in $\text{In}_{2-x}\text{Sn}_x\text{Se}_3$ polycrystalline layers. , 2015, , . | | 0 |
| 69 | Optical-memory switching and oxygen detection based on the CVT grown $\hat{\Gamma}^3$ - and $\hat{\Gamma}^{\pm}$ -phase In ₂ Se ₃ . Sensors and Actuators B: Chemical, 2015, 209, 811-819. | 7.8 | 15 |
| 70 | Polarized optical sensing and band-edge transitions in Ag(In _{0.5} Al _{0.5})S ₂ . Applied Physics Express, 2015, 8, 025801. | 2.4 | 1 |
| 71 | Surface Sensing and Optical Behavior of Al-Based Silver Chalcopyrites. Journal of Electronic Materials, 2015, 44, 984-990. | 2.2 | 0 |
| 72 | Influence of rhenium on the structural and optical properties of molybdenum disulfide. Japanese Journal of Applied Physics, 2015, 54, 04DH05. | 1.5 | 21 |

| # | ARTICLE | IF | CITATIONS |
|----|---|------|-----------|
| 73 | Structural property and optical band edge of Ag(In _{0.5} Al _{0.5})S ₂ . Journal of Materials Science: Materials in Electronics, 2015, 26, 3766-3771. | 2.2 | 0 |
| 74 | Integrated digital inverters based on two-dimensional anisotropic ReS ₂ field-effect transistors. Nature Communications, 2015, 6, 6991. | 12.8 | 505 |
| 75 | Single-Layer ReS ₂ : Two-Dimensional Semiconductor with Tunable In-Plane Anisotropy. ACS Nano, 2015, 9, 11249-11257. | 14.6 | 353 |
| 76 | Optical behavior and structural property of CuAlS ₂ and AgAlS ₂ wide-bandgap chalcopyrites. Applied Optics, 2014, 53, E7. | 1.8 | 10 |
| 77 | Piezoreflectance study of near band edge excitonic-transitions of mixed-layered crystal Mo(SxSe _{1-x}) ₂ solid solutions. Journal of Applied Physics, 2014, 115, . | 2.5 | 20 |
| 78 | Structural phase transition and erasable optically memorized effect in layered \hat{I}^3 -In ₂ Se ₃ crystals. Journal of Applied Physics, 2014, 115, . | 2.5 | 20 |
| 79 | Analyzing a steady-state phenomenon using an ensemble of sequential transient events: A proof of concept on photocurrent of bacteriorhodopsin upon continuous photoexcitation. Journal of Applied Physics, 2014, 116, 144701. | 2.5 | 0 |
| 80 | Transport properties in semiconducting NbS ₂ nanoflakes. Applied Physics Letters, 2014, 105, . | 3.3 | 39 |
| 81 | Formation and stability of point defects in monolayer rhenium disulfide. Physical Review B, 2014, 89, . | 3.2 | 151 |
| 82 | Monolayer behaviour in bulk ReS ₂ due to electronic and vibrational decoupling. Nature Communications, 2014, 5, 3252. | 12.8 | 906 |
| 83 | Large-area nanoscale farmland-like surfaces of one-dimensional NbO ₂ nanorods with multi-growth directions: studies on the purple-blue photoluminescence and low-field electron emissions. Journal of Materials Chemistry C, 2014, 2, 8667-8672. | 5.5 | 23 |
| 84 | Amorphous effect on the advancing of wide-range absorption and structural-phase transition in \hat{I}^3 -In ₂ Se ₃ polycrystalline layers. Scientific Reports, 2014, 4, 4764. | 3.3 | 38 |
| 85 | Photoluminescence mechanisms of metallic Zn nanospheres, semiconducting ZnO nanoballoons and metal-semiconductor Zn/ZnO nanospheres. Scientific Reports, 2014, 4, 6967. | 3.3 | 84 |
| 86 | Optically decomposed near-band-edge structure and excitonic transitions in Ga ₂ S ₃ . Scientific Reports, 2014, 4, 6143. | 3.3 | 52 |
| 87 | Characterization of nitrogen doped p-type ZnO thin films prepared by reactive ion beam sputter deposition. Surface and Coatings Technology, 2013, 231, 492-495. | 4.8 | 14 |
| 88 | Direct vapor transport synthesis of ZnGa ₂ O ₄ nanowires with superior photocatalytic activity. Journal of Alloys and Compounds, 2013, 555, 325-329. | 5.5 | 22 |
| 89 | Thickness-tunable band gap modulation in \hat{I}^3 -In ₂ Se ₃ . RSC Advances, 2013, 3, 24896. | 3.6 | 26 |
| 90 | The study of optical band edge property of bismuth oxide nanowires \hat{I}^{\pm} -Bi ₂ O ₃ . Optics Express, 2013, 21, 11965. | 3.4 | 96 |

| # | ARTICLE | IF | CITATIONS |
|-----|---|-----|-----------|
| 91 | Optical characterization of InAlAs/InGaAs metamorphic high-electron mobility transistor structures with tensile and compressive strain. <i>Thin Solid Films</i> , 2013, 529, 217-221. | 1.8 | 2 |
| 92 | Surface Oxide Effect on Optical Sensing and Photoelectric Conversion of In_2Se_3 Hexagonal Microplates. <i>ACS Applied Materials & Interfaces</i> , 2013, 5, 2269-2277. | 8.0 | 91 |
| 93 | The study of rapid thermal annealing on arsenic-doped ZnO for the p-type ZnO formation. <i>Journal of Crystal Growth</i> , 2013, 362, 193-196. | 1.5 | 10 |
| 94 | NIR and UV enhanced photon detector made by diindium trichalcogenides. <i>Optical Materials Express</i> , 2013, 3, 1420. | 3.0 | 15 |
| 95 | Optical properties of wide-band-gap chalcopyrite $\text{CuAl}(\text{Se}_{0.5}\text{S}_{0.5})_2$ evaluated by thermoreflectance spectroscopy. <i>Optical Materials Express</i> , 2013, 3, 480. | 3.0 | 5 |
| 96 | Practical and User-Friendly Circuits and System Design for Signals' Sensing and Generation. <i>Circuits and Systems</i> , 2013, 04, 387-392. | 0.1 | 3 |
| 97 | Dichroic Electro-Optical Behavior of Rhenium Sulfide Layered Crystal. <i>Crystal Structure Theory and Applications</i> , 2013, 02, 65-69. | 0.1 | 10 |
| 98 | Nitrogen Doping Effect on Optical Property of Gallium Oxide Nanowires. <i>ECS Journal of Solid State Science and Technology</i> , 2012, 1, P78-P81. | 1.8 | 5 |
| 99 | Surface sensing behavior and band edge properties of AgAlS_2 : Experimental observations in optical, chemical, and thermoreflectance spectroscopy. <i>AIP Advances</i> , 2012, 2, . | 1.3 | 13 |
| 100 | Optical characterization of band-edge property of In_6S_7 compound. <i>Applied Physics Letters</i> , 2012, 100, . | 3.3 | 20 |
| 101 | Structural and Band-Edge Properties of $\text{Cu}(\text{Al}_x\text{In}_{1-x})\text{S}_2$ ($0 \leq x \leq 1$) Series Chalcopyrite Semiconductors. <i>Solid State Phenomena</i> , 2012, 194, 133-138. | 0.3 | 3 |
| 102 | Room-temperature wide-range photoluminescence and semiconducting characteristics of two-dimensional pure metallic Zn nanoplates. <i>RSC Advances</i> , 2012, 2, 2123. | 3.6 | 26 |
| 103 | The study of below and above band-edge imperfection states in In_2S_3 solar energy materials. <i>Physica B: Condensed Matter</i> , 2012, 407, 3052-3055. | 2.7 | 11 |
| 104 | Cathodoluminescence and Field-Emission Properties of In^{2+} -Ga $_2\text{O}_3$ Nanobelts. <i>Journal of Electronic Materials</i> , 2012, 41, 3056-3061. | 2.2 | 5 |
| 105 | Influence of anionic substitution on the electrolyte electroreflectance study of band edge transitions in single crystal $\text{Cu}_2\text{ZnSn}(\text{S}_x\text{Se}_{1-x})_4$ solid solutions. <i>Optical Materials</i> , 2012, 34, 1362-1365. | 3.6 | 57 |
| 106 | Enhanced photoelectric-conversion yield in niobium-incorporated In_2S_3 with intermediate band. <i>Journal of Materials Chemistry</i> , 2011, 21, 10518. | 6.7 | 57 |
| 107 | Piezoreflectance and Raman Characterization of $\text{Mo}_x\text{W}_x\text{S}_2$ Layered Mixed Crystals. <i>Solid State Phenomena</i> , 2011, 170, 55-59. | 0.3 | 8 |
| 108 | Electronic structure and optical property of $\text{As}_2(\text{Te}_{1-x}\text{S})_3$ and $\text{As}_2(\text{Te}_{1-x}\text{Se})_3$ crystals. <i>Journal of Alloys and Compounds</i> , 2011, 509, 7198-7204. | 5.5 | 6 |

| # | ARTICLE | IF | CITATIONS |
|-----|---|-----|-----------|
| 109 | Direct Optical Observation of Band-Edge Excitons, Band Gap, and Fermi Level in Degenerate Semiconducting Oxide Nanowires In_2O_3 . Journal of Physical Chemistry C, 2011, 115, 25088-25096. | 3.1 | 58 |
| 110 | Enhanced Photocatalytic Activity in In_2O_3 Nanobelts. Journal of the American Ceramic Society, 2011, 94, 3117-3122. | 3.8 | 63 |
| 111 | Synthesis of In_2O_3 nanowires as a broadband emitter. Applied Physics A: Materials Science and Processing, 2011, 102, 105-108. | 2.3 | 11 |
| 112 | Single crystal growth and characterization of copper aluminum indium disulfide chalcopyrites. Journal of Crystal Growth, 2011, 317, 52-59. | 1.5 | 10 |
| 113 | Temperature Dependent Crystal-Field Splitting and Band-Edge Characteristic in $\text{Cu}(\text{Al}_x\text{In}_{1-x})\text{S}_2$ Series Solar Energy Materials. Journal of the Electrochemical Society, 2011, 158, H554. | 2.9 | 8 |
| 114 | Optical Characterization of Electronic Structure of CuInS_2 and CuAlS_2 Chalcopyrite Crystals. Solid State Phenomena, 2011, 170, 21-24. | 0.3 | 1 |
| 115 | Effect of temperature on lateral growth of ZnO grains grown by MOCVD. Ceramics International, 2010, 36, 69-73. | 4.8 | 38 |
| 116 | Growth and characterization of near-band-edge transitions in In_2S_3 single crystals. Journal of Crystal Growth, 2010, 312, 2718-2723. | 1.5 | 52 |
| 117 | Nitrogen-doped ZnO prepared by capillaritron reactive ion beam sputtering deposition. Applied Surface Science, 2010, 256, 4153-4156. | 6.1 | 5 |
| 118 | Thermoreflectance characterization of band-edge excitonic transitions in CuAlS_2 ultraviolet solar-cell material. Applied Physics Letters, 2010, 96, . | 3.3 | 23 |
| 119 | The study of surface photoconductive response in indium sulfide crystals. Journal Physics D: Applied Physics, 2010, 43, 415301. | 2.8 | 17 |
| 120 | Temperature-dependent photoconductivity in In_2S_3 single crystals. Journal of Applied Physics, 2010, 108, . | 2.5 | 29 |
| 121 | Polarized-thermoreflectance study of the band-edge transitions in $\text{Cu}(\text{Al}_{0.05}\text{In}_{0.05})\text{S}_2$ solar-energy related crystal. Optics Express, 2010, 18, 3820. | 3.4 | 9 |
| 122 | Thermoreflectance characterization of In_2O_3 thin-film nanostrips. Optics Express, 2010, 18, 16360. | 3.4 | 57 |
| 123 | Electronic Structure and $E_{[1]}$ Excitons of CuInS_2 Energy-Related Crystals Studied by Temperature-Dependent Thermoreflectance Spectroscopy. Journal of the Electrochemical Society, 2010, 157, H219. | 2.9 | 11 |
| 124 | Structural and luminescent property of gallium chalcogenides $\text{GaSe}_{1-x}\text{S}_x$ layer compounds. Journal of Materials Science: Materials in Electronics, 2009, 20, 207-210. | 2.2 | 9 |
| 125 | In-plane anisotropic electrical and optical properties of gold-doped rhenium disulphide. Journal of Materials Science: Materials in Electronics, 2009, 20, 476-479. | 2.2 | 7 |
| 126 | Optical and electrical characteristics of GaAs/InGaAs quantum-well device. Journal of Alloys and Compounds, 2009, 471, 567-569. | 5.5 | 9 |

| # | ARTICLE | IF | CITATIONS |
|-----|--|-----|-----------|
| 127 | Optical anisotropy of Au-doped ReS ₂ crystals. Journal of Alloys and Compounds, 2009, 480, 94-96. | 5.5 | 16 |
| 128 | Optical anisotropy of near band-edge transitions in zinc oxide nanostructures. Journal of Alloys and Compounds, 2009, 480, 50-53. | 5.5 | 5 |
| 129 | Thermoelectric properties of ZnS-Sb alloys doped with In. Journal of Alloys and Compounds, 2009, 480, 73-75. | 5.5 | 21 |
| 130 | Optical investigation of band-edge structure and built-in electric field of AlGaIn/GaN heterostructures by means of thermoreflectance, photoluminescence, and contactless electroreflectance spectroscopy. Optics Letters, 2009, 34, 3604. | 3.3 | 9 |
| 131 | High room-temperature photoluminescence of one-dimensional Ta ₂ O ₅ nanorod arrays. Nanotechnology, 2009, 20, 445708. | 2.6 | 59 |
| 132 | Temperature-dependent photoreflectance and photoluminescence characterization of the subband structure and built-in electric field of GaAs/GaInAs graded-channel high electron mobility transistor structures. Semiconductor Science and Technology, 2009, 24, 035013. | 2.0 | 3 |
| 133 | Optical properties of near band-edge transitions in well-aligned and tilted ZnO nanostructures. Journal Physics D: Applied Physics, 2008, 41, 165410. | 2.8 | 4 |
| 134 | Characterization of indirect and direct interband transitions of anatase TiO ₂ by thermoreflectance spectroscopy. Applied Physics Letters, 2008, 93, . | 3.3 | 40 |
| 135 | Compensation and Carrier Conduction in Synthetic Fe _{1-x} Ni _x S ₂ (0 ≤ x ≤ 0.1) Single Crystals. Journal of the Electrochemical Society, 2008, 155, H254. | 2.9 | 2 |
| 136 | Band-edge properties of layered germanium dichalcogenides. Physical Review B, 2007, 76, . | 3.2 | 2 |
| 137 | Comprehensive Characterization of AlGaAs-InGaAs-GaAs Composite-Channel High-Electron Mobility Transistor. Journal of the Electrochemical Society, 2007, 154, H951. | 2.9 | 13 |
| 138 | Optical anisotropy of ZnO nanocrystals on sapphire by thermoreflectance spectroscopy. Optics Letters, 2007, 32, 2765. | 3.3 | 12 |
| 139 | Optical characterization of a GaAs/In _{0.5} (Al _x Ga _{1-x}) _{0.5} P/GaAs heterostructure cavity by piezoreflectance spectroscopy. Optics Express, 2007, 15, 13886. | 3.4 | 5 |
| 140 | Characterization of As ₂ (Se _{1-x} S _x) ₃ series glass system. Journal of Alloys and Compounds, 2007, 427, 305-309. | 5.5 | 1 |
| 141 | Dichroic optical and electrical properties of rhenium dichalcogenides layer compounds. Journal of Alloys and Compounds, 2007, 442, 245-248. | 5.5 | 10 |
| 142 | Improved InP-based double heterojunction bipolar transistors. Physica Status Solidi C: Current Topics in Solid State Physics, 2007, 4, 1680-1684. | 0.8 | 0 |
| 143 | Band-Edge Transitions of a Metallorganic Chemical Vapor Deposited ZnO Film on Si by Thermoreflectance Spectroscopy. Electrochemical and Solid-State Letters, 2006, 9, G312. | 2.2 | 2 |
| 144 | Photoconductance and photoresponse of layer compound photodetectors in the UV-visible region. Review of Scientific Instruments, 2006, 77, 113102. | 1.3 | 30 |

| # | ARTICLE | IF | CITATIONS |
|-----|---|-----|-----------|
| 145 | Characterization of near band-edge properties of synthetic p-FeS ₂ iron pyrite from electrical and photoconductivity measurements. Journal of Alloys and Compounds, 2006, 422, 321-327. | 5.5 | 13 |
| 146 | Improved InAlGaP-based heterostructure field-effect transistors. Semiconductor Science and Technology, 2006, 21, 540-543. | 2.0 | 7 |
| 147 | Characterization of Gap States in an Amorphous SiN _[sub x] Film Grown on GaAs Substrate Using Modulation Spectroscopic Techniques. Electrochemical and Solid-State Letters, 2006, 9, G181. | 2.2 | 1 |
| 148 | Photoreflectance and Photoluminescence Study of In _[sub x] Ga _[sub 1-x] As-GaAs Graded-Channel High Electron Mobility Transistors. Journal of the Electrochemical Society, 2006, 153, G966. | 2.9 | 2 |
| 149 | Optical properties of the interband transitions of layered gallium sulfide. Journal of Applied Physics, 2006, 100, 083508. | 2.5 | 78 |
| 150 | Thermoreflectance characterization of interband transitions of In _{0.34} Al _{0.66} As _{0.85} Sb _{0.15} epitaxy on InP. Applied Physics Letters, 2006, 89, 191906. | 3.3 | 4 |
| 151 | Crystal structure and electronic structure of GaSe _{1-x} S _x series layered solids. Journal of Crystal Growth, 2005, 279, 321-328. | 1.5 | 46 |
| 152 | Characterization of Ge ₂ (Se _{1-x} S _x) ₂ series layered crystals grown by vertical Bridgman method. Journal of Crystal Growth, 2005, 281, 377-383. | 1.5 | 7 |
| 153 | Visible luminescence and structural property of GaSe _{1-x} S _x (0 ≤ x ≤ 1) series layered crystals. Solid State Communications, 2005, 136, 591-594. | 1.9 | 25 |
| 154 | Thermoreflectance study of the electronic structure of Ge ₂ (Se _{1-x} S _x) ₂ . Physical Review B, 2005, 72, . | 3.2 | 11 |
| 155 | Optical study of the structural change in ReS ₂ single crystals using polarized thermoreflectance spectroscopy. Optics Express, 2005, 13, 8. | 3.4 | 37 |
| 156 | Practical photoluminescence and photoreflectance spectroscopic system for optical characterization of semiconductor devices. Optics Express, 2005, 13, 3951. | 3.4 | 11 |
| 157 | Temperature Dependence of the Band-Edge Transitions of ZnCdBeSe. Japanese Journal of Applied Physics, 2004, 43, 459-466. | 1.5 | 14 |
| 158 | Polarization sensitive behaviour of the band-edge transitions in ReS ₂ and ReSe ₂ layered semiconductors. Journal of Physics Condensed Matter, 2004, 16, 5937-5944. | 1.8 | 33 |
| 159 | Practical thermoreflectance design for optical characterization of layer semiconductors. Review of Scientific Instruments, 2004, 75, 1098-1102. | 1.3 | 50 |
| 160 | High-resolution and easily implemented spectral measured system used for optical characterization of optoelectronic materials and devices. Optical Engineering, 2004, 43, 1628. | 1.0 | 2 |
| 161 | Optical properties of GaSe _{1-x} S _x series layered semiconductors grown by vertical Bridgman method. Materials Chemistry and Physics, 2004, 88, 313-317. | 4.0 | 44 |
| 162 | Preparation and characterization of Ni-incorporated FeS ₂ single crystals. Journal of Crystal Growth, 2004, 270, 535-541. | 1.5 | 25 |

| # | ARTICLE | IF | CITATIONS |
|-----|--|-----|-----------|
| 163 | Growth and characterization of tungsten and molybdenum-doped ReSe ₂ single crystals. Journal of Alloys and Compounds, 2004, 383, 63-68. | 5.5 | 14 |
| 164 | Optical property of the near band-edge transitions in rhenium disulfide and diselenide. Journal of Alloys and Compounds, 2004, 383, 74-79. | 5.5 | 49 |
| 165 | Photoreflectance study of the excitonic transitions of rhenium disulphide layer compounds. Physical Review B, 2002, 66, . | 3.2 | 48 |
| 166 | Preparation and characterization of molybdenum-doped ReS ₂ single crystals. Journal of Physics Condensed Matter, 2002, 14, 4737-4746. | 1.8 | 12 |
| 167 | Electrical and optical anisotropic properties of rhenium-doped molybdenum disulphide. Journal of Alloys and Compounds, 2001, 317-318, 208-212. | 5.5 | 24 |
| 168 | In-plane anisotropy of the optical and electrical properties of ReS ₂ and ReSe ₂ layered crystals. Journal of Alloys and Compounds, 2001, 317-318, 222-226. | 5.5 | 70 |
| 169 | Novel electronic design for double-modulation spectroscopy of semiconductor and semiconductor microstructures. Review of Scientific Instruments, 2001, 72, 4218-4222. | 1.3 | 1 |
| 170 | Polarized electrolyte-electroreflectance study of ReS ₂ and ReSe ₂ layered semiconductors. Journal of Physics Condensed Matter, 2001, 13, 8145-8152. | 1.8 | 13 |
| 171 | A practical and inexpensive design for measuring the radiation patterns and luminescent spectra of optoelectronic devices. Review of Scientific Instruments, 2001, 72, 3103-3107. | 1.3 | 6 |
| 172 | Temperature dependent polarized-piezoreflectance study of GaInP. Journal of Physics Condensed Matter, 2000, 12, 2183-2192. | 1.8 | 3 |
| 173 | Temperature dependence piezoreflectance study of the effect of doping MoS ₂ with rhenium. Journal of Physics Condensed Matter, 2000, 12, 3441-3449. | 1.8 | 18 |
| 174 | In-plane anisotropy of the optical and electrical properties of layered ReS ₂ crystals. Journal of Physics Condensed Matter, 1999, 11, 5367-5375. | 1.8 | 57 |
| 175 | Electronic structure of ReS ₂ and ReSe ₂ from first-principles calculations, photoelectron spectroscopy, and electrolyte electroreflectance. Physical Review B, 1999, 60, 15766-15771. | 3.2 | 56 |
| 176 | The electrical transport properties of ReS ₂ and ReSe ₂ layered crystals. Solid State Communications, 1999, 111, 635-640. | 1.9 | 44 |
| 177 | Crystal structure and band-edge transitions of ReS ₂ and ReSe ₂ layered compounds. Journal of Physics and Chemistry of Solids, 1999, 60, 1797-1804. | 4.0 | 69 |
| 178 | Growth and characterization of rhenium-doped MoS ₂ single crystals. Journal of Crystal Growth, 1999, 205, 543-547. | 1.5 | 53 |
| 179 | An electrolyte electroreflectance study of ReS ₂ . Solid State Communications, 1998, 109, 19-22. | 1.9 | 4 |
| 180 | Temperature dependence of energies and broadening parameters of the band-edge excitons of single crystals. Journal of Physics Condensed Matter, 1998, 10, 9317-9328. | 1.8 | 51 |

| # | ARTICLE | IF | CITATIONS |
|-----|---|-----|-----------|
| 181 | Absorption-edge anisotropy in ReS_2 and ReSe_2 layered semiconductors. <i>Physical Review B</i> , 1998, 58, 16130-16135. | 3.2 | 94 |
| 182 | Piezoreflectance study of band-edge excitons of ReS_2 single crystals. <i>Physical Review B</i> , 1998, 58, 12575-12578. | 3.2 | 18 |
| 183 | Temperature dependence of energies and broadening parameters of the band-edge excitons of ReS_2 and ReSe_2 . <i>Physical Review B</i> , 1997, 55, 15608-15613. | 3.2 | 60 |
| 184 | Optical absorption of ReS_2 and ReSe_2 single crystals. <i>Journal of Applied Physics</i> , 1997, 81, 6380-6383. | 2.5 | 56 |
| 185 | Temperature dependent study of the band edge excitons of ReS_2 and ReSe_2 . <i>Journal of Alloys and Compounds</i> , 1997, 262-263, 92-96. | 5.5 | 13 |
| 186 | Piezoreflectance study of the band-edge excitons of ReS_2 . <i>Solid State Communications</i> , 1997, 103, 19-23. | 1.9 | 10 |
| 187 | Inactivation of coupled respiration of mitochondria by inorganic arsenate and partial restoration by ATP. <i>Biochemical and Biophysical Research Communications</i> , 1972, 49, 690-697. | 2.1 | 7 |
| 188 | Microstructures and Thermoelectric Properties of $(\text{Bi}_{1-x}\text{Te}_3)_x(\text{CdTe})_{0.3}$ Composites. <i>Solid State Phenomena</i> , 0, 170, 41-46. | | 0 |
| 189 | Thermoelectric Properties of $\text{Pb}_{1-x}\text{Cd}_x\text{Se}$ Crystals Grown by Vertical Bridgman Method. <i>Solid State Phenomena</i> , 0, 194, 148-152. | 0.3 | 0 |
| 190 | Composition Dependent Band Gaps of Single Crystal $\text{Cu}_2\text{ZnSn}(\text{S}_x\text{Se}_{1-x})_4$ Solid Solutions. <i>Solid State Phenomena</i> , 0, 194, 139-143. | | 6 |
| 191 | Optical Characterization of Undoped and Au-Doped MoS_2 Single Crystals. <i>Applied Mechanics and Materials</i> , 0, 627, 50-53. | 0.2 | 4 |